



512Kx8 MONOLITHIC SRAM

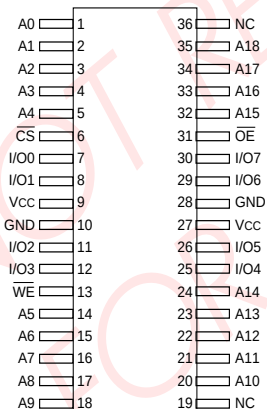
FEATURES

- Access Times 15, 17, 20ns
- Revolutionary, Center Power/Ground Pinout
JEDEC Approved
 - 36 lead Ceramic SOJ (Package 100)
 - 36 lead Ceramic Flat Pack (Package 226)
- Evolutionary, Corner Power/Ground Pinout
JEDEC Approved
 - 32 pin Ceramic DIP (Package 300)
 - 32 lead Ceramic SOJ (Package 101)
 - 32 lead Ceramic Flat Pack (Package 220)
- Low Voltage Operation:
 - $3.3V \pm 10\%$ Power Supply
- BiCMOS:
 - Radiation Tolerant with Epitaxial Layer Die
- Commercial and Industrial Temperature Ranges
- TTL Compatible Inputs and Outputs
- Fully Static Operation:
 - No clock or refresh required.
- Three State Output

REVOLUTIONARY PINOUT

36 FLAT PACK
36 CSOJ

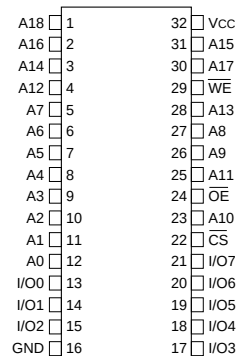
TOP VIEW



EVOLUTIONARY PINOUT

32 DIP
32 CSOJ (DE)
32 FLAT PACK (FE)

TOP VIEW



PIN DESCRIPTION

A0-18	Address Inputs
I/O0-7	Data Input/Output
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
Vcc	Power Supply
GND	Ground



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-40	+85	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	4.6	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	4.6	V

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	3.0	3.6	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V
Operating Temp.	T _A	-40	+85	°C

TRUTH TABLE

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active
L	H	H	Out Disable	High Z	Active

CAPACITANCE

(T_A = +25°C)

Parameter	Symbol	Condition	Max	Unit
Input capacitance	C _{IN}	V _{IN} = 0V, f = 1.0MHz	12	pF
Output capacitance	C _{OUT}	V _{OUT} = 0V, f = 1.0MHz	12	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS (V_{CC} = 3.3V, GND = 0V, T_A = -40°C to +85°C)

Parameter	Sym	Conditions	Min		Units
				Max	
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	$\overline{CS}$ = V _{IH} , $\overline{OE}$ = V _{IH} , V _{OUT} = GND to V _{CC}		10	μA
Operating Supply Current	I _{CC}	$\overline{CS}$ = V _{IL} , $\overline{OE}$ = V _{IH} , f = 5MHz, V _{CC} = 5.5		120	mA
Standby Current	I _{SB}	$\overline{CS}$ = V _{IH} , $\overline{OE}$ = V _{IH} , f = 5MHz, V _{CC} = 5.5		15	mA
Output Low Voltage	V _{OL}	I _{OL} = 8mA		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -4.0mA	2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V



AC CHARACTERISTICS ($V_{CC} = 3.3V, GND = 0V, T_A = -40^{\circ}C$ to $+85^{\circ}C$)

Parameter	Symbol	-15		-17		-20		Units
		Min	Max	Min	Max	Min	Max	
Read Cycle								
Read Cycle Time	t_{RC}	15		17		20		ns
Address Access Time	t_{AA}		15		17		20	ns
Output Hold from Address Change	t_{OH}	0		0		0		ns
Chip Select Access Time	t_{ACS}		15		17		20	ns
Output Enable to Output Valid	t_{OE}		7		8		10	ns
Chip Select to Output in Low Z	t_{CLZ}^1	2		2		2		ns
Output Enable to Output in Low Z	t_{OLZ}^1	0		0		0		ns
Chip Disable to Output in High Z	t_{CHZ}^1		7		8		10	ns
Output Disable to Output in High Z	t_{OHZ}^1		7		8		10	ns

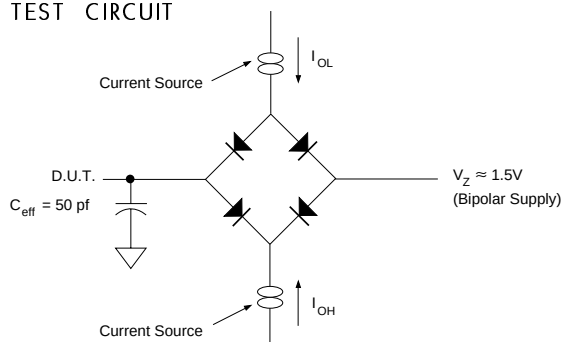
1. This parameter is guaranteed by design but not tested.

AC CHARACTERISTICS ($V_{CC} = 3.3V, GND = 0V, T_A = -40^{\circ}C$ to $+85^{\circ}C$)

Parameter	Symbol	-15		-17		-20		Units
		Min	Max	Min	Max	Min	Max	
Write Cycle								
Write Cycle Time	t_{WC}	15		17		20		ns
Chip Select to End of Write	t_{CW}	10		12		14		ns
Address Valid to End of Write	t_{AW}	10		12		14		ns
Data Valid to End of Write	t_{DW}	8		9		10		ns
Write Pulse Width	t_{WP}	12		14		14		ns
Address Setup Time	t_{AS}	0		0		0		ns
Address Hold Time	t_{AH}	0		0		0		ns
Output Active from End of Write	t_{OW}^1	2		3		3		ns
Write Enable to Output in High Z	t_{WHZ}^1		8		8		9	ns
Data Hold Time	t_{DH}	0		0		0		ns

1. This parameter is guaranteed by design but not tested.

AC TEST CIRCUIT



AC TEST CONDITIONS

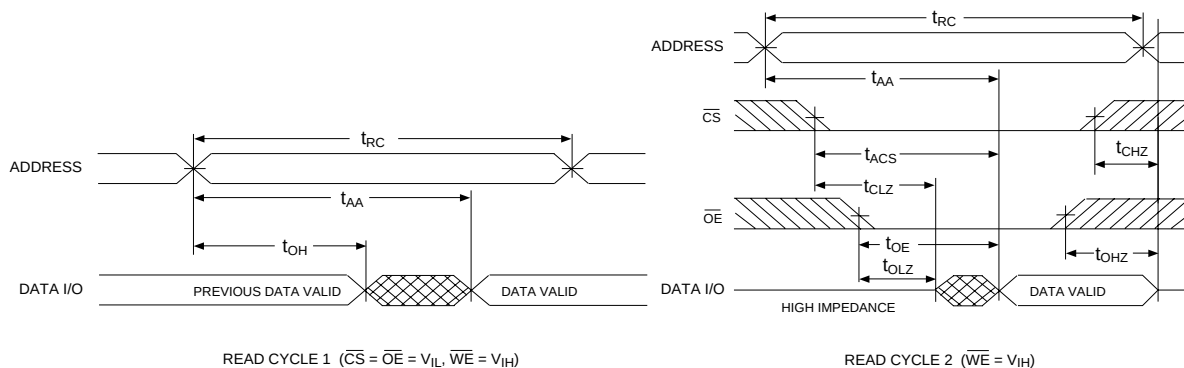
Parameter	Typ	Unit
Input Pulse Levels	$V_{IL} = 0, V_{IH} = 2.5$	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:

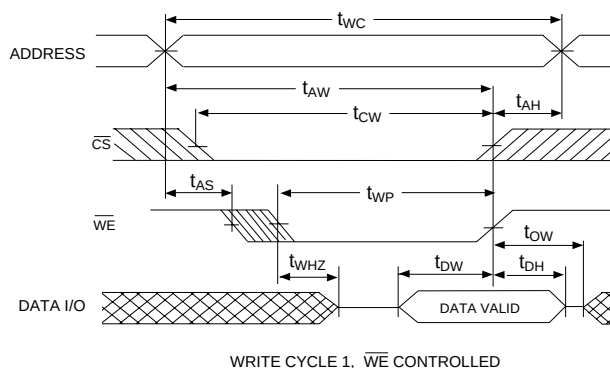
V_Z is programmable from -2V to +7V.
 I_{OL} & I_{OH} programmable from 0 to 16mA.
 Tester Impedance $Z_0 = 75 \Omega$.
 V_Z is typically the midpoint of V_{OH} and V_{OL} .
 I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
 ATE tester includes jig capacitance.



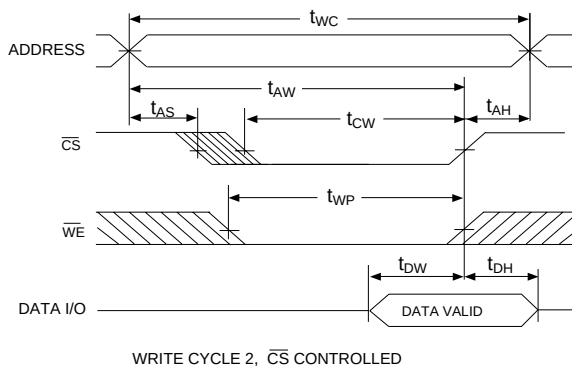
TIMING WAVEFORM - READ CYCLE



WRITE CYCLE - $\overline{WE}$ CONTROLLED

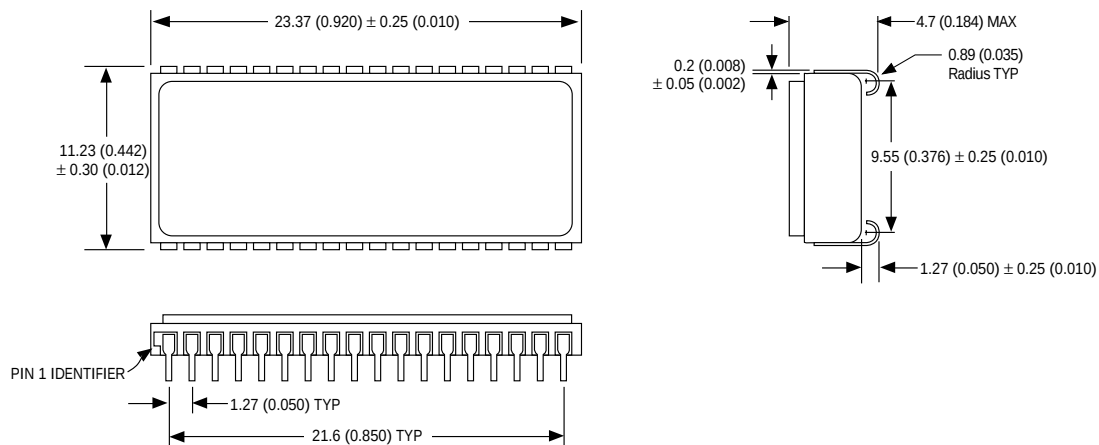


WRITE CYCLE - $\overline{CS}$ CONTROLLED



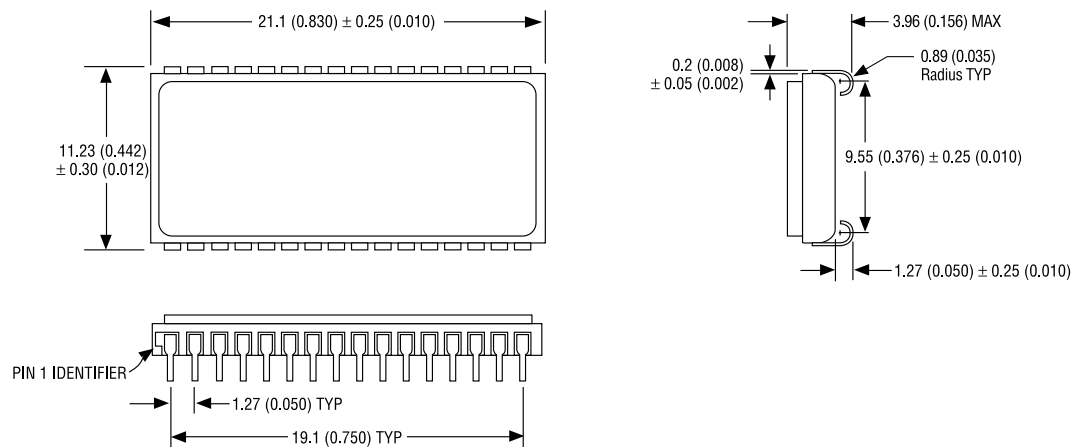


PACKAGE 100: 36 LEAD, CERAMIC SOJ



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

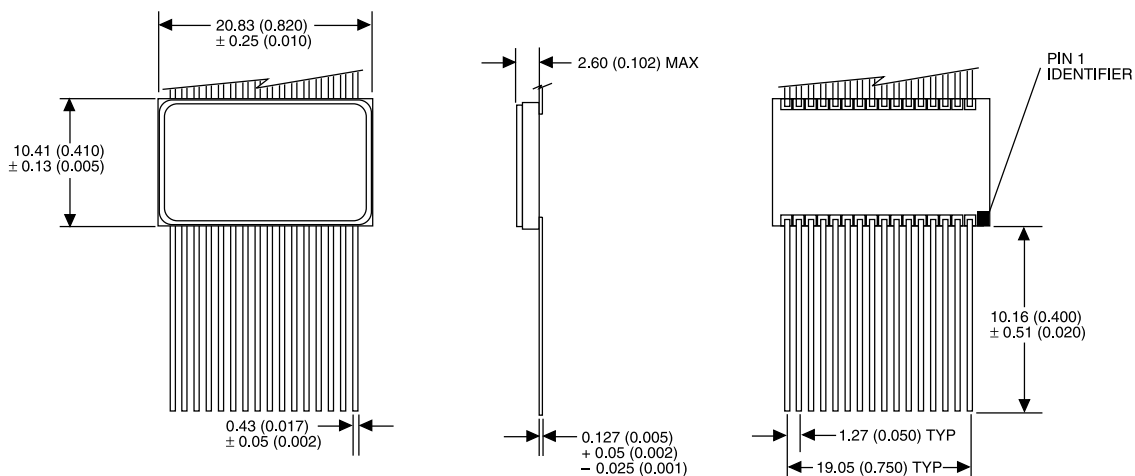
PACKAGE 101: 32 LEAD, CERAMIC SOJ



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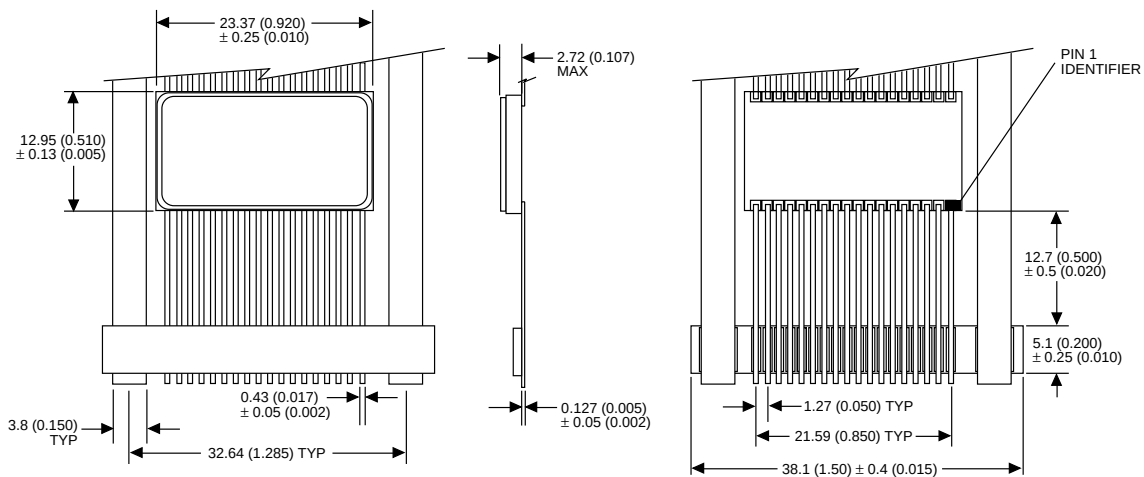


PACKAGE 220: 32 LEAD, CERAMIC FLAT PACK



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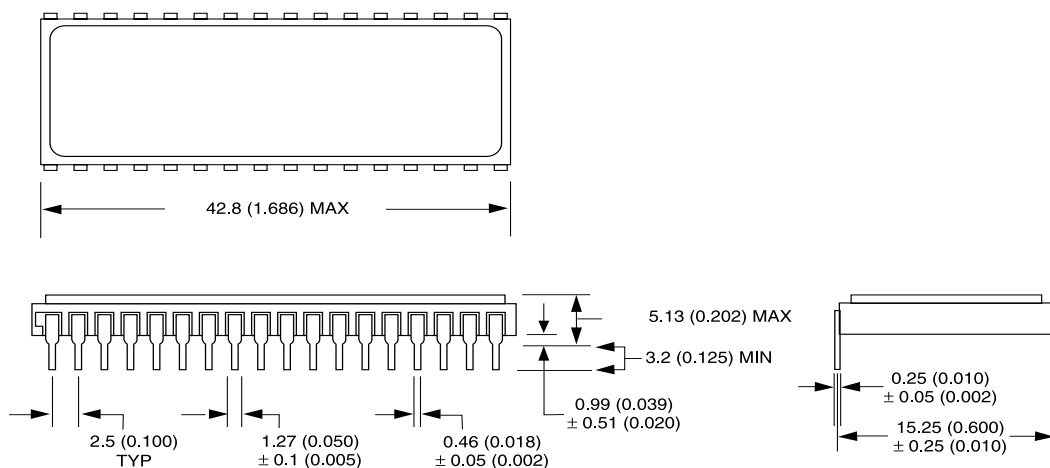
PACKAGE 226: 36 LEAD, CERAMIC FLAT PACK



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



PACKAGE 300: 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



ORDERING INFORMATION

W M S 512K 8 B V - XXX X X E X

LEAD FINISH:

Blank = Gold plated leads

A = Solder dip leads

E = Epitaxial Layer

DEVICE GRADE:

I = Industrial -40°C to +85°C

C = Commercial 0°C to +70°C

PACKAGE:

C = 32 Pin Ceramic .600" DIP (Package 300)

DE = 32 Lead Ceramic SOJ (Package 101) Evolutionary

DJ = 36 Lead Ceramic SOJ (Package 100)

F = 36 Lead Ceramic Flat Pack (Package 226)

FE = 32 Lead Ceramic Flat Pack (Package 220)

ACCESS TIME (ns)

Low Voltage Supply 3.3V $\pm$ 10%

BiCMOS

ORGANIZATION, 512K x 8

SRAM

MONOLITHIC

WHITE ELECTRONIC DESIGNS CORP.